

Electrical Specifications ($T_C=25^\circ\text{C}$ unless otherwise noted)

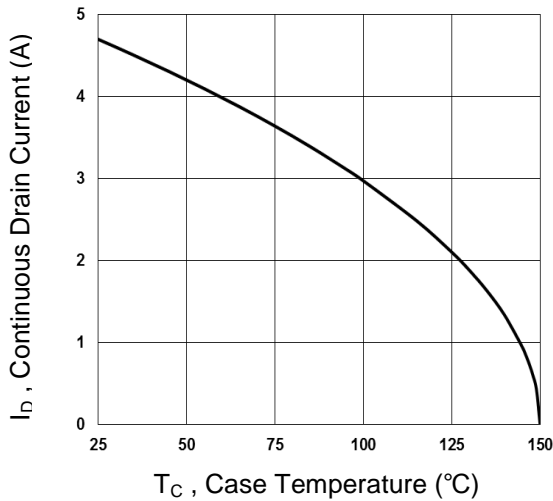
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV_{DSS}	-20	--	--	V
Drain-Source On-State Resistance	$V_{GS} = -4.5V, I_D = -3A$	$R_{DS(ON)}$	--	42	50	mΩ
	$V_{GS} = -2.5V, I_D = -2A$		--	57	65	
	$V_{GS} = -1.8V, I_D = -1A$		--	75	85	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	$V_{GS(TH)}$	-0.3	-0.6	-0.8	V
Zero Gate Voltage Drain Current	$V_{DS} = -20V, V_{GS} = 0V$	I_{DSS}	--	--	-1	μA
	$V_{DS} = -16V, T_J = 125^{\circ}C$		--	--	-10	
Gate Body Leakage	$V_{GS} = \pm 10V, V_{DS} = 0V$	I_{GSS}	--	--	±100	nA
Forward Transconductance ^(Note 2)	$V_{DS} = -10V, I_D = -3A$	g_{fs}	--	7	--	S
Dynamic						
Total Gate Charge ^(Note 2,3)	$V_{DS} = -10V, I_D = -3A,$ $V_{GS} = -4.5V$	Q_g	--	9.6	--	nC
Gate-Source Charge ^(Note 2,3)		Q_{gs}	--	1.6	--	
Gate-Drain Charge ^(Note 2,3)		Q_{gd}	--	2	--	
Input Capacitance	$V_{DS} = -10V, V_{GS} = 0V,$ $f = 1.0MHz$	C_{iss}	--	850	--	pF
Output Capacitance		C_{oss}	--	70	--	
Reverse Transfer Capacitance		C_{rss}	--	55	--	
Switching						
Turn-On Delay Time ^(Note 2,3)	$V_{DD} = -10V, I_D = -1A,$ $V_{GS} = -4.5V, R_{GEN} = 25\Omega$	$t_{d(on)}$	--	6	--	ns
Turn-On Rise Time ^(Note 2,3)		t_r	--	21.6	--	
Turn-Off Delay Time ^(Note 2,3)		$t_{d(off)}$	--	51	--	
Turn-Off Fall Time ^(Note 2,3)		t_f	--	13.8	--	
Source-Drain Diode Ratings and Characteristic						
Maximum Continuous Drain-Source Diode Forward Current	Integral reverse diode in the MOSFET	I_S	--	--	-4.7	A
Maximum Pulse Drain-Source Diode Forward Current		I_{SM}	--	--	-18.8	A
Diode-Source Forward Voltage	$V_{GS} = 0V, I_S = -1A$	V_{SD}	--	--	-1	V

Note:

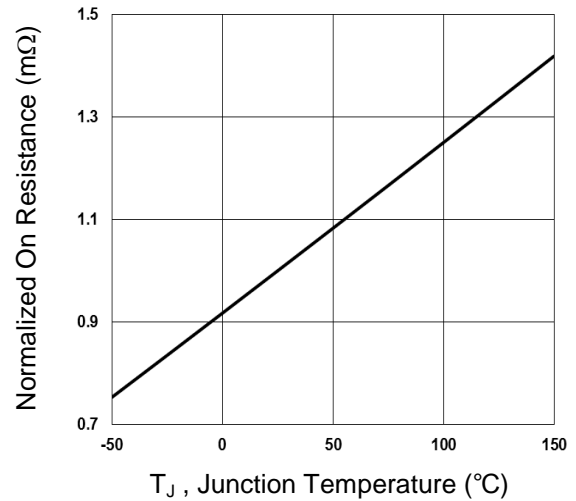
- Pulse width limited by safe operating area
- Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- Switching time is essentially independent of operating temperature.

Electrical Characteristics Curves

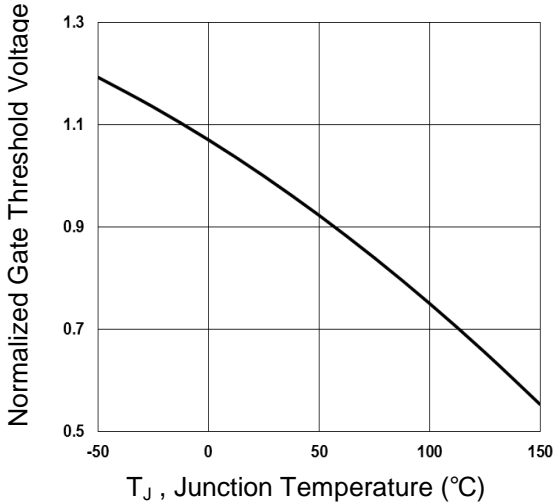
Continuous Drain Current vs. T_C



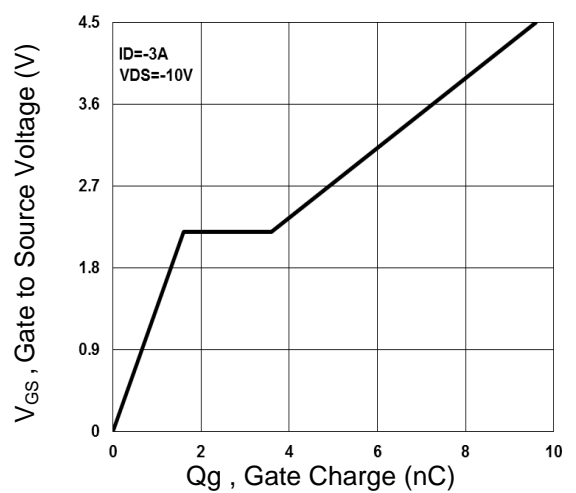
Normalized $R_{DS(on)}$ vs. T_J



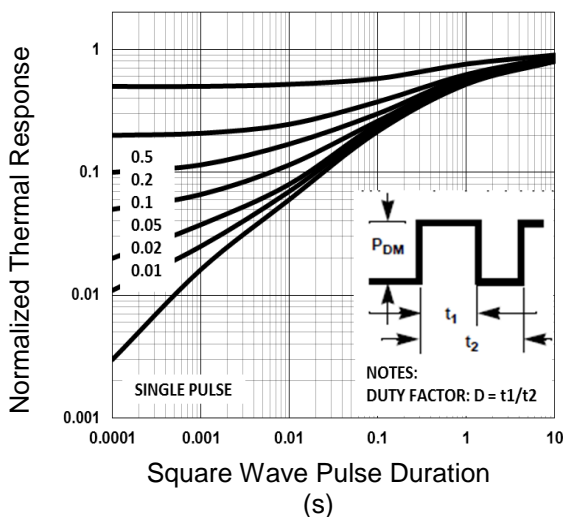
Normalized V_{th} vs. T_J



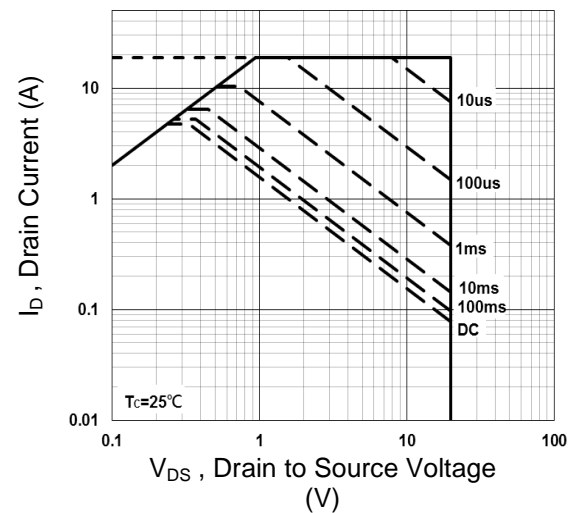
Gate Charge Waveform



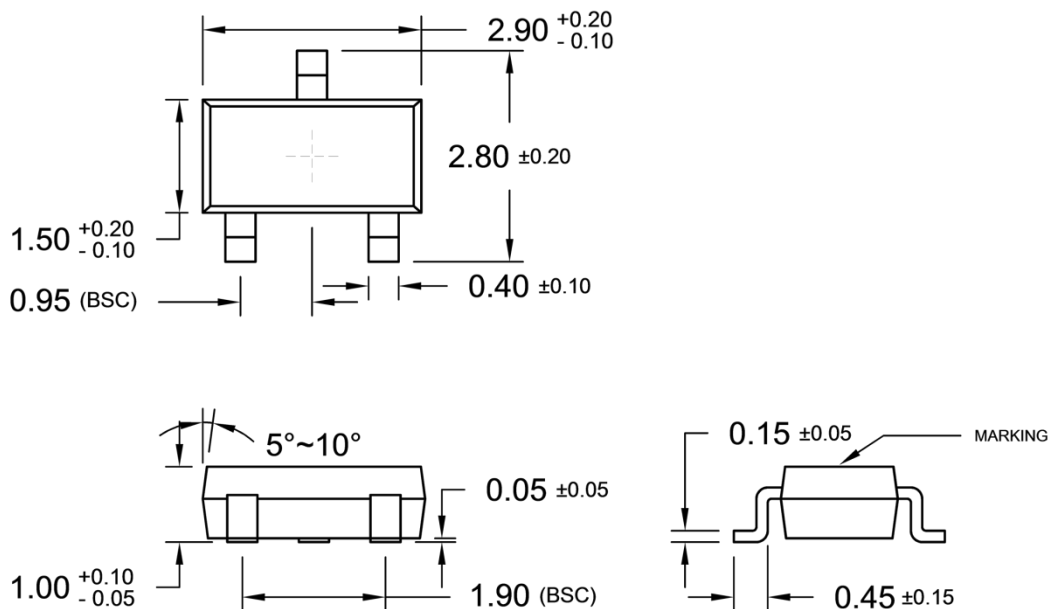
Normalized Transient Impedance



Maximum Safe Operation Area

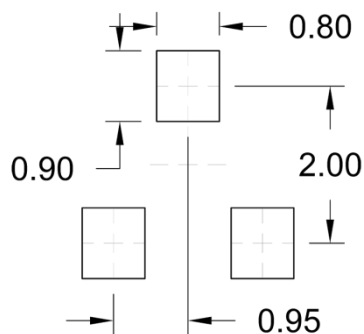


SOT-23 Mechanical Drawing

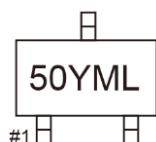


Unit: Millimeters

SUGGESTED PAD LAYOUT (Unit: Millimeters)



Marking Diagram



- 50** = Device Code
- Y** = Year Code
- M** = Month Code for Halogen Free Product
(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)
- L** = Lot Code

TSM500P02CX

20V P-Channel Power MOSFET

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